



# P3MPC018



## 30V P-Channel MOSFETs

### General Description

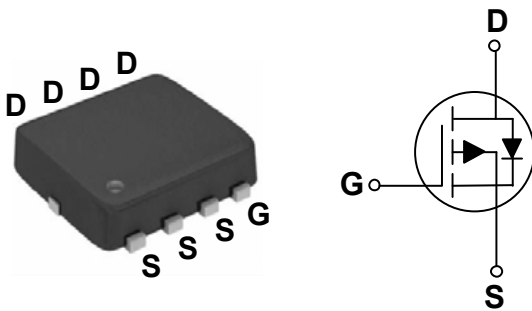
The P3MPC018 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a battery protection or in other Switching application.

$BV_{DSS}$	$R_{DS(ON)}$	$I_D$
-30 V	18 m $\Omega$	-30 A

### Features

- $R_{DS(ON)} \leq 18m\Omega @ V_{GS} = -10V$
- Fast switching
- Green Device Available

PPAK3X3 Pin Configuration



### Applications

- Lithium battery protection
- Wireless impact
- Mobile phone fast charging

### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-30	V
$V_{GS}$	Gate-Source Voltage	$\pm 25$	V
$I_D$	Drain Current - Continuous ( $T_C=25^\circ\text{C}$ )	-32	A
	Drain Current - Continuous ( $T_C=100^\circ\text{C}$ )	-20	A
$I_{DM}$	Drain Current - Pulsed (NOTE 1)	-65	A
EAS	Single Pulse Avalanche Energy (NOTE 2)	72.2	mJ
IAS	Avalanche Current	-38	A
$P_D$	Power Dissipation ( $T_C=25^\circ\text{C}$ )	29	W
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
Marking Code		PC018	

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	---	75	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	4.32	$^\circ\text{C/W}$



Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> = -250uA	-30	---	---	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = -24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> = -24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	-5	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±25V, V <sub>DS</sub> =0V	---	---	±100	nA

On Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance (NOTE 1)	V <sub>GS</sub> = -10V, I <sub>D</sub> = -10A	---	15.5	18	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -5A	---	20.5	28	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> = -250uA	-1.0	-1.4	-2.5	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> = -5V, I <sub>D</sub> = -15A	---	19	---	S

Dynamic and switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q <sub>g</sub>	Total Gate Charge (-4.5V)	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -15A	---	12.5	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	5.4	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	5	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -10V, R <sub>G</sub> = 3.3Ω, I <sub>D</sub> = -15A	---	4.4	---	nS
T <sub>r</sub>	Rise Time		---	11.2	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	34	---	
T <sub>f</sub>	Fall Time		---	18	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, F= 1MHz	---	1345	---	pF
C <sub>OSS</sub>	Output Capacitance		---	194	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	158	---	
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0A, f=1MHZ	---	13	---	Ω

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current (NOTE 4)	V <sub>G</sub> = V <sub>D</sub> = 0V, Force Current	---	---	-32	A
I <sub>SM</sub>	Pulsed Source Current (NOTE 1 & 4)		---	---	-65	A
V <sub>SD</sub>	Diode Forward Voltage (NOTE 1)	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A, T <sub>J</sub> =25°C	---	---	-1.2	V
trr	Reverse Recovery Time	I <sub>F</sub> = -15A, di/dt=100A/us,	---	12.4	---	nS
Qrr	Reverse Recovery Charge	T <sub>J</sub> =25°C	---	5	---	nC

NOTES :

1. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
2. The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=-25V, V<sub>GS</sub>=-10V, L=0.1mH, I<sub>AS</sub>=-38A.
3. The power dissipation is limited by 150°C junction temperature.
4. The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.



Characteristics Curves

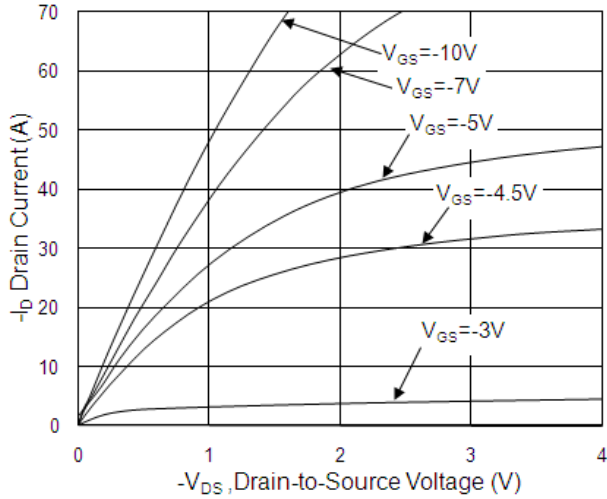


Fig.1 Typical Output Characteristics

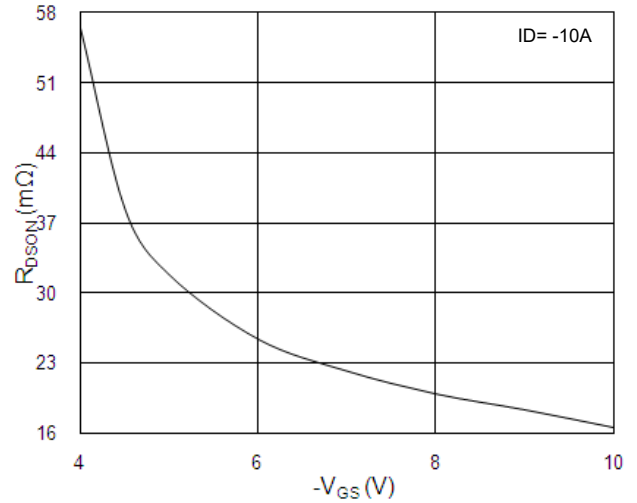


Fig.2 On-Resistance v.s Gate-Source

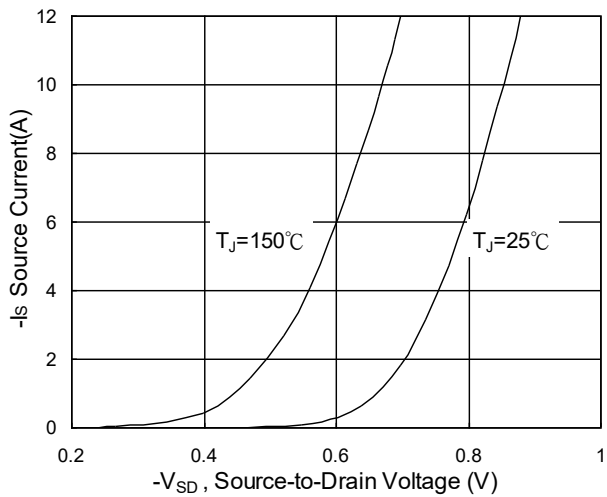


Fig.3 Forward Characteristics of Reverse

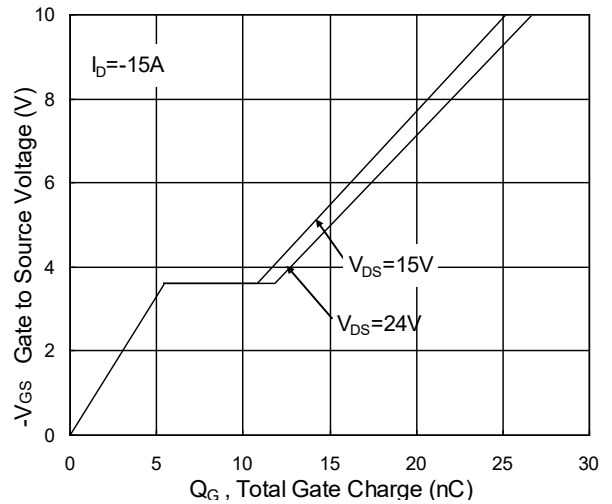


Fig.4 Gate-Charge Characteristics

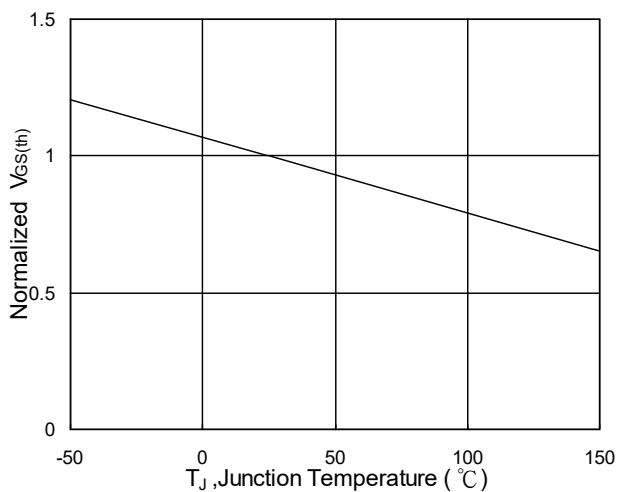


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$

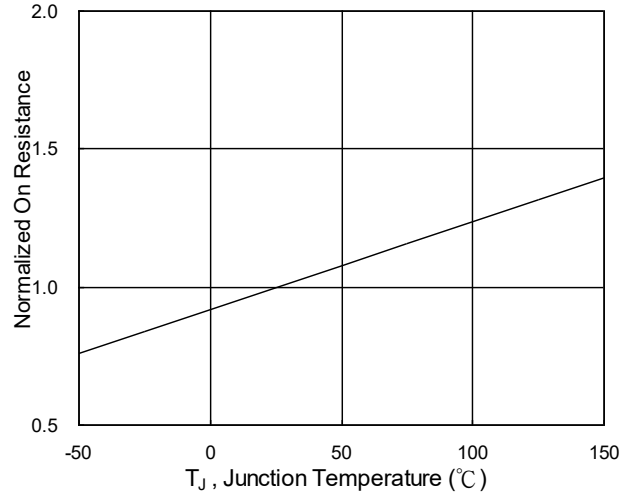


Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$



Characteristics Curves

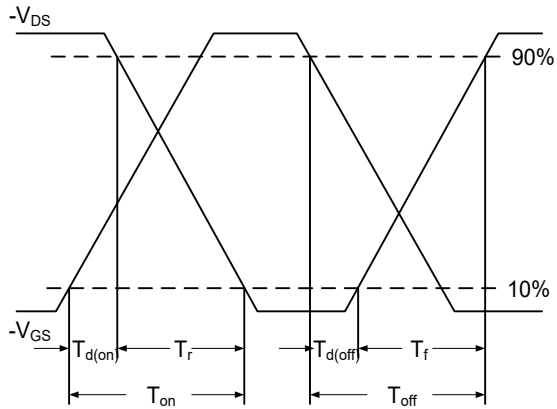
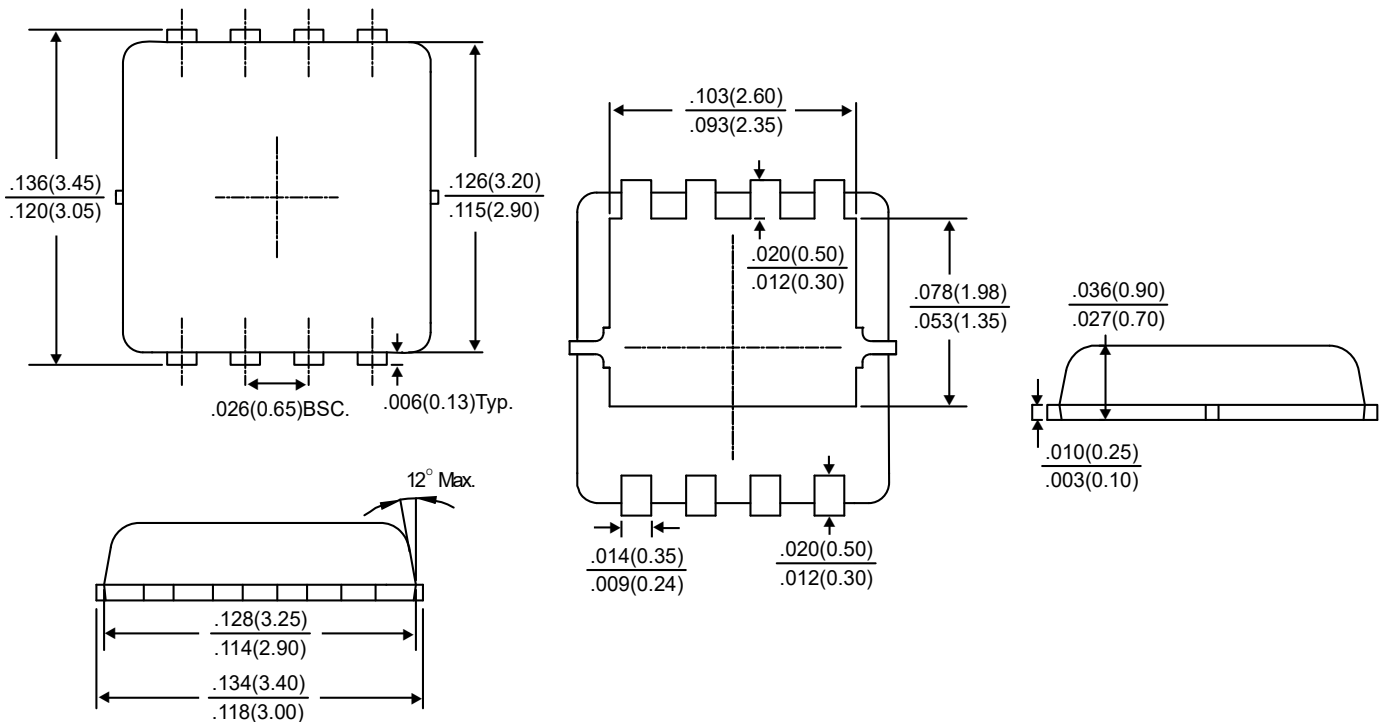


Fig. 7 Switching Time Waveform

Package Outline Dimensions



PPAK3X3

Dimensions in inches and (millimeters)



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